SDI Review Form 1.6

Journal Name:	**Physical Science International Journal**
Manuscript Number:	**Ms_PSIJ_24297**
Title of the Manuscript:	**Characterisation of Defects Induced by Ion-implantation Processing of P+N Shallow Junction Devices.**
Type of the Article	**Original Research Article**

General guideline for Peer Review process:

This journal's peer review policy states that **NO** manuscript should be rejected only on the basis of '**lack of Novelty**', provided the manuscript is scientifically robust and technically sound.
To know the complete guideline for Peer Review process, reviewers are requested to visit this link:

(http://www.sciencedomain.org/page.php?id=sdi-general-editorial-policy#Peer-Review-Guideline)

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PART 1: **Review Comments**

	Reviewer's comment	**Author's comment** *(if agreed with reviewer, correct the manuscript and highlight that part in the manuscript. It is mandatory that authors should write his/her feedback here)*
Compulsory REVISION comments	**A)Abstract** **Describing language in a manuscript should be accurate.** **e.g.** **Line16** show more or less constant defect **B)Introduction** **Authors should add more latest developing trends and references and quote some paper from journals such as Physical Science International Journal** **C) METHODOLOGY** **Fig.1 is not clear.** **D) RESULTS AND DISCUSSION** **(1)Line 168 The defect level E (0.24) appears as a shoulder in the experimental samples, especially in samples P06 and P10. Authors should make more illustrations of the shoulder peak.** **(2)Line 178 the signal height does not change with the implantation energy. What does such phenomenon mean?** **(3) The nature of the defects could be viewed as a result of the amorphising implants creating a large number of Si interstitials. This is not quite clear that due to the amorphising implants, authors should delete the content or make clear explanation here.**	

	E)Conclusions **Language should be re-organized.** **F)Reference** **Format is not correct, and authors should make corrections according to journal's requirements.** **e.g.** **[5]** Journal of Appl. Phys. 83 (1998) 3008 **[6]** *Phys. Rev*. B **69**, (2004). **[10]** Thermal and Mechanical Properties of Materials, 2005. **The title and year, page format should be uniform.**	
Minor REVISION comments	**(1)Line 215CONCLUSIONs→CONCLUSIONS** **(2)Line9 the device were of were evaluated** **(3)Line12 of all of both types** **(4)Line212 the main text should be departed form the figure title** **(5)Line217 The defect E(0.42) can only be associated with Ge implantation asit is not observed in reference sample P21.**	
Optional/General comments		

Reviewer Details:

Name:	**Hao Wang**
Department, University & Country	**Northeastern University, USA**